## Low-Voltage CMOS Octal Buffer

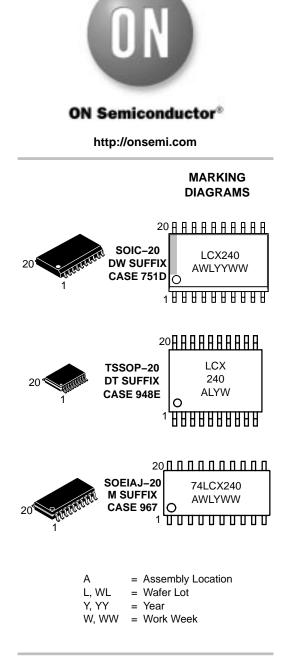
# With 5 V–Tolerant Inputs and Outputs (3–State, Inverting)

The MC74LCX240 is a high performance, inverting octal buffer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V<sub>I</sub> specification of 5.5 V allows MC74LCX240 inputs to be safely driven from 5 V devices. The MC74LCX240 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

Current drive capability is 24 mA at the outputs. The Output Enable  $(\overline{OE})$  input, when HIGH, disables the outputs by placing them in a HIGH Z condition.

## Features

- Designed for 2.3 to 3.6 V V<sub>CC</sub> Operation
- 5 V Tolerant Interface Capability With 5 V TTL Logic
- Supports Live Insertion and Withdrawal
- $I_{OFF}$  Specification Guarantees High Impedance When  $V_{CC} = 0$  V
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (10 µA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V Machine Model >200 V
- Pb–Free Packages are Available\*



## ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

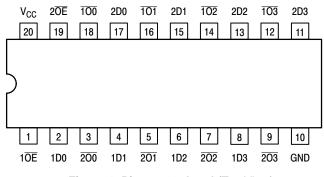
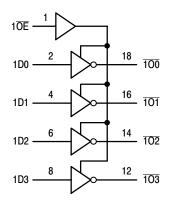


Figure 1. Pinout: 20-Lead (Top View)



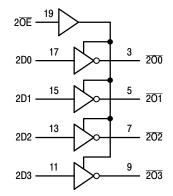


Figure 2. LOGIC DIAGRAM

## **PIN NAMES**

Pins	Function
n <del>OE</del>	Output Enable Inputs
1Dn, 2Dn	Data Inputs
1On, 2On	3–State Outputs

## **TRUTH TABLE**

INP	UTS	OUTPUTS
10E 20E	1Dn 2Dn	10n, 20n
L	L	Н
L	Н	L
н	Х	Z

High Voltage Level Н =

Low Voltage Level L =

= High Impedance State

Z X = High or Low Voltage Level and Transitions Are Acceptable; for I<sub>CC</sub> reasons, DO NOT FLOAT Inputs

## MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_0 \le +7.0$	Output in 3-State	V
		$-0.5 \leq V_O \leq V_{CC} + 0.5$	Note 1	V
I <sub>IK</sub>	DC Input Diode Current	-50	V <sub>I</sub> < GND	mA
I <sub>OK</sub>	DC Output Diode Current	-50	V <sub>O</sub> < GND	mA
		+50	$V_{O} > V_{CC}$	mA
lo	DC Output Source/Sink Current	±50		mA
I <sub>CC</sub>	DC Supply Current Per Supply Pin	±100		mA
I <sub>GND</sub>	DC Ground Current Per Ground Pin	±100		mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Output in HIGH or LOW State. I<sub>O</sub> absolute maximum rating must be observed.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Para	meter	Min	Тур	Max	Unit
V <sub>CC</sub>	Supply Voltage	Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
V <sub>O</sub>	Output Voltage	(HIGH or LOW State) (3–State)	0 0		V <sub>CC</sub> 5.5	V
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> =	3.0 V – 3.6 V			-24	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> =	3.0 V – 3.6 V			24	mA
I <sub>OH</sub>	HIGH Level Output Current, V <sub>CC</sub> =	2.7 V – 3.0 V			-12	mA
I <sub>OL</sub>	LOW Level Output Current, V <sub>CC</sub> =	2.7 V – 3.0 V			12	mA
T <sub>A</sub>	Operating Free–Air Temperature		-40		+85	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate, V V <sub>CC</sub> = $3.0$ V	/ <sub>IN</sub> from 0.8 V to 2.0 V,	0		10	ns/V

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC74LCX244DWR2	SOIC-20	1000 Tape & Reel
MC74LCX244DR2G	SOIC-20 (Pb-Free)	1000 Tape & Reel
MC74LCX244DTR2	TSSOP-20*	2000 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*This package is inherently Pb-Free.

## DC ELECTRICAL CHARACTERISTICS

			T <sub>A</sub> = -40°C	C to +85°C	
Symbol	Characteristic	Condition	Min	Мах	Unit
V <sub>IH</sub>	HIGH Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}$	2.0		V
V <sub>IL</sub>	LOW Level Input Voltage (Note 2)	$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$		0.8	V
V <sub>OH</sub>	HIGH Level Output Voltage	2.7 V $\leq$ V_{CC} $\leq$ 3.6 V; I_{OH} = –100 $\mu A$	V <sub>CC</sub> – 0.2		V
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OH} = -24 \text{ mA}$	2.2		

2. These values of V<sub>I</sub> are used to test DC electrical characteristics only.

## DC ELECTRICAL CHARACTERISTICS (Continued)

			T <sub>A</sub> = -40°	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V <sub>OL</sub>	LOW Level Output Voltage	2.7 V $\leq$ V_{CC} $\leq$ 3.6 V; I_{OL} = 100 $\mu A$		0.2	V
		$V_{CC} = 2.7 \text{ V}; \text{ I}_{OL} = 12 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OL} = 16 \text{ mA}$		0.4	
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OL} = 24 \text{ mA}$		0.55	
l <sub>l</sub>	Input Leakage Current	$2.7 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}; \text{ 0 V} \leq \text{V}_{\text{I}} \leq 5.5 \text{ V}$		±5.0	μΑ
I <sub>OZ</sub>	3-State Output Current	$\begin{array}{l} 2.7 \leq V_{CC} \leq 3.6 \text{ V}; \ 0V \leq V_O \leq 5.5 \text{ V}; \\ V_I = V_{IH} \text{ or } V_{\ IL} \end{array}$		±5.0	μΑ
I <sub>OFF</sub>	Power-Off Leakage Current	$V_{CC} = 0 \text{ V}; \text{ V}_{1} \text{ or } \text{V}_{O} = 5.5 \text{ V}$		10	μA
I <sub>CC</sub>	Quiescent Supply Current	$2.7 \leq V_{CC} \leq 3.6$ V; V_I = GND or V_{CC}		10	μΑ
		$2.7 \leq V_{CC} \leq 3.6$ V; $3.6 \leq V_{I} \text{ or } V_{O} \leq 5.5$ V		±10	μA
$\Delta I_{CC}$	Increase in I <sub>CC</sub> per Input	$2.7 \leq V_{CC} \leq 3.6 \text{ V}; \text{ V}_{IH} = V_{CC} - 0.6 \text{ V}$		500	μΑ

## **AC CHARACTERISTICS** ( $t_R = t_F = 2.5 \text{ ns}$ ; $C_L = 50 \text{ pF}$ ; $R_L = 500 \Omega$ )

				Limits		
			T,	<sub>A</sub> = −40°C to ·	+85°C	
			V <sub>CC</sub> = 3.0	V to 3.6 V	V <sub>CC</sub> = 2.7 V	1
Symbol	Parameter	Waveform	Min	Max	Мах	Unit
t <sub>PLH</sub> t <sub>PHL</sub>	Propagation Delay Input to Output	1	1.5 1.5	6.5 6.5	7.5 7.5	ns
t <sub>PZH</sub> t <sub>PZL</sub>	Output Enable Time to High and Low Level	2	1.5 1.5	8.0 8.0	9.0 9.0	ns
t <sub>PHZ</sub> t <sub>PLZ</sub>	Output Disable Time From High and Low Level	2	1.5 1.5	7.0 7.0	8.0 8.0	ns
t <sub>OSHL</sub> t <sub>OSLH</sub>	Output-to-Output Skew (Note 3)			1.0 1.0		ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>); parameter guaranteed by design.

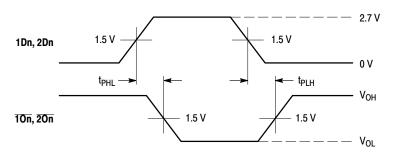
## DYNAMIC SWITCHING CHARACTERISTICS

			T	₄ = +25°	С	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
V <sub>OLP</sub>	Dynamic LOW Peak Voltage (Note 4)	$V_{CC}$ = 3.3 V, $C_L$ = 50 pF, $V_{IH}$ = 3.3 V, $V_{IL}$ = 0 V		0.8		V
V <sub>OLV</sub>	Dynamic LOW Valley Voltage (Note 4)	$V_{CC}$ = 3.3 V, $C_L$ = 50 pF, $V_{IH}$ = 3.3 V, $V_{IL}$ = 0 V		0.8		V

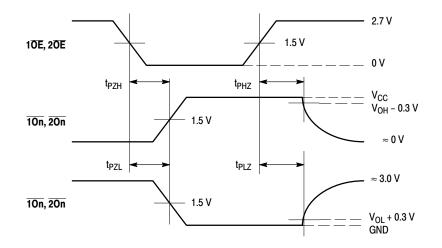
4. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

## **CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Condition	Typical	Unit
C <sub>IN</sub>	Input Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	7	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	8	pF
C <sub>PD</sub>	Power Dissipation Capacitance	10 MHz, $V_{CC}$ = 3.3 V, $V_{I}$ = 0 V or $V_{CC}$	25	pF

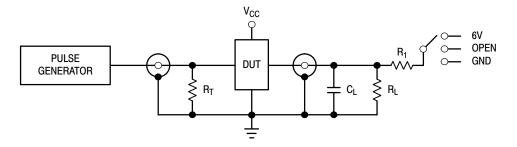


**WAVEFORM 1 - PROPAGATION DELAYS**  $t_{R} = t_{F} = 2.5$  ns, 10% to 90%; f = 1 MHz;  $t_{W} = 500$  ns



WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES  $t_{R} = t_{F} = 2.5 \text{ ns}, 10\% \text{ to } 90\%; \text{ f} = 1 \text{ MHz}; t_{W} = 500 \text{ ns}$ 





TEST	SWITCH
t <sub>PLH</sub> , t <sub>PHL</sub>	Open
t <sub>PZL</sub> , t <sub>PLZ</sub>	6V
Open Collector/Drain $t_{PLH}$ and $t_{PHL}$	6V
t <sub>PZH</sub> , t <sub>PHZ</sub>	GND

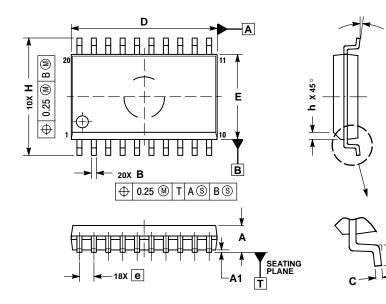
 $C_L$  = 50pF or equivalent (Includes jig and probe capacitance)  $R_L$  =  $R_1$  = 500 $\Omega$  or equivalent

 $R_T = Z_{OUT}$  of pulse generator (typically 50 $\Omega$ )

Figure 4. Test Circuit

## PACKAGE DIMENSIONS

SOIC-20 **DW SUFFIX** CASE 751D-05 **ISSUE G** 

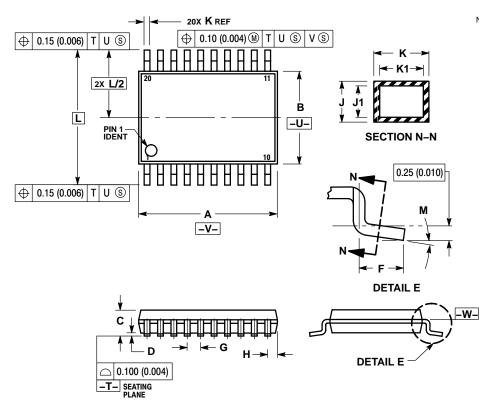


NOTES:

- 1. 2.
- DIMENSIONS ARE IN MILLIMETERS. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD 3. PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B 5. DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
C	0.23	0.32	
D	12.65	12.95	
E	7.40	7.60	
е	1.27	BSC	
н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

TSSOP-20 DT SUFFIX CASE 948E-02 ISSUE B



NOTES:

DITES:
 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS. SHALL NOT EXCEED 0.15 (0.006) PER SUDE

SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER

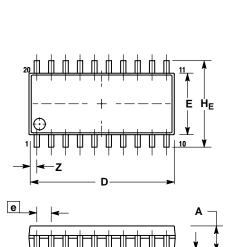
SIDE. 5. DIMENSION K DOES NOT INCLUDE 5. DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K
 DIMENSION AT MAXIMUM MATERIAL
 CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN

FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-. 7

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.27	0.37	0.011	0.015
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
Μ	0°	8°	0 °	8°

## PACKAGE DIMENSIONS

SOEIAJ-20 **M SUFFIX** CASE 967-01 ISSUE O



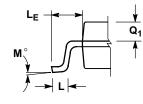
A<sub>1</sub>

□ 0.10 (0.004)

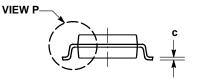
– b

0.13 (0.005) 🕅

 $\oplus$ 



DETAIL P



- NOTES:
  DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SUDE
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
Е	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
Z		0.81		0.032

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